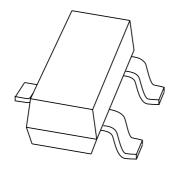
### DISCRETE SEMICONDUCTORS

# DATA SHEET



BC846; BC847; BC848 NPN general purpose transistors

Product specification Supersedes data of 1999 Apr 23





# NPN general purpose transistors

BC846; BC847; BC848

#### **FEATURES**

• Low current (max. 100 mA)

• Low voltage (max. 65 V).

### **APPLICATIONS**

• General purpose switching and amplification.

#### **DESCRIPTION**

NPN transistor in a SOT23 plastic package. PNP complements: BC856, BC857 and BC858.

#### **MARKING**

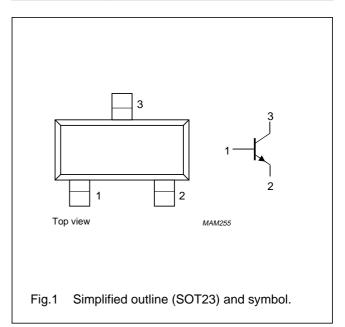
TYPE NUMBER	MARKING CODE(1)
BC846	1D*
BC846A	1A*
BC846B	1B*
BC847	1H*
BC847A	1E*
BC847B	1F*
BC847C	1G*
BC848B	1K*

#### Note

1. \* = p: made in Hong Kong.

### **PINNING**

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



<sup>\* =</sup> t: made in Malaysia.

# NPN general purpose transistors

BC846; BC847; BC848

### **LIMITING VALUES**

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	RAMETER CONDITIONS		MAX.	UNIT	
V <sub>CBO</sub>	collector-base voltage	open emitter				
	BC846		_	80	V	
	BC847		_	50	V	
	BC848		_	30	V	
V <sub>CEO</sub>	collector-emitter voltage	open base				
	BC846		_	65	V	
	BC847		_	45	V	
	BC848		_	30	V	
V <sub>EBO</sub>	emitter-base voltage	open collector				
	BC846; BC847		_	6	V	
	BC848		_	5	V	
I <sub>C</sub>	collector current (DC)		_	100	mA	
I <sub>CM</sub>	peak collector current		_	200	mA	
I <sub>BM</sub>	peak base current		_	200	mA	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	250	mW	
T <sub>stg</sub>	storage temperature		-65	+150	°C	
Tj	junction temperature		_	150	°C	
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C	

### Note

1. Transistor mounted on an FR4 printed-circuit board, standard footprint.

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER CONDITIONS		VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air; note 1	500	K/W

### Note

1. Transistor mounted on an FR4 printed-circuit board, standard footprint.

# NPN general purpose transistors

BC846; BC847; BC848

### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C; unless otherwise specified.

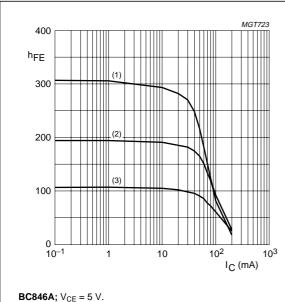
SYMBOL PARAMETER		PARAMETER CONDITIONS		TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0	_	_	15	nA
		$V_{CB} = 30 \text{ V}; I_{E} = 0;$ $T_{j} = 150 ^{\circ}\text{C}$	_	-	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0	_	Ī-	100	nA
h <sub>FE</sub>	DC current gain	$I_C = 10 \mu A; V_{CE} = 5 V$				
	BC846A; BC847A		-	90	-	
	BC846B; BC847B; BC848B		_	150	-	
	BC847C		_	270	-	
	DC current gain	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V				
	BC846		110	-	450	
	BC847		110	-	800	
	BC846A; BC847A		110	180	220	
	BC846B; BC847B; BC848B		200	290	450	
	BC847C		420	520	800	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	90	250	mV
		$I_C = 100 \text{ mA}; I_B = 5 \text{ mA};$ note 1	_	200	600	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	700	_	mV
		$I_C = 100 \text{ mA}; I_B = 5 \text{ mA};$ note 1	_	900	_	mV
V <sub>BE</sub>	base-emitter voltage	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V	580	660	700	mV
		$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$	_	Ī-	770	mV
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = I_{e} = 0;$ f = 1 MHz	_	2.5	_	pF
f <sub>T</sub>	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	100	_	_	MHz
F	noise figure	$I_C = 200 \mu A; V_{CE} = 5 V;$ $R_S = 2 k\Omega; f = 1 kHz;$ B = 200 Hz	_	2	10	dB

### Note

1. Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02.$ 

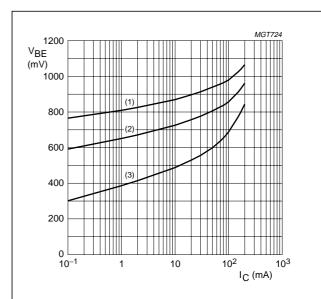
### NPN general purpose transistors

### BC846; BC847; BC848



- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

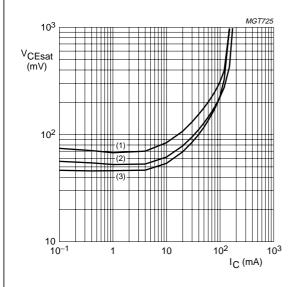
Fig.2 DC current gain as a function of collector current; typical values.



**BC846A**; V<sub>CE</sub> = 5 V.

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

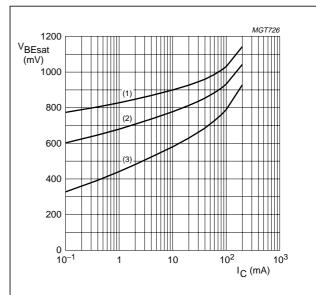
Fig.3 Base-emitter voltage as a function of collector current; typical values.



**BC846A**;  $I_C/I_B = 20$ .

- (1) T<sub>amb</sub> = 150 °C.
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



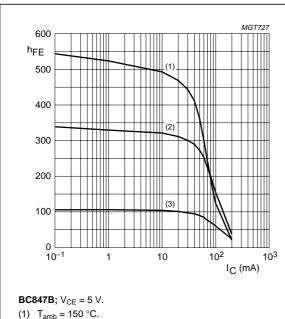
**BC846A**;  $I_C/I_B = 10$ .

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

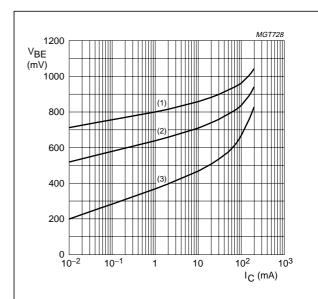
### NPN general purpose transistors

### BC846; BC847; BC848



- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

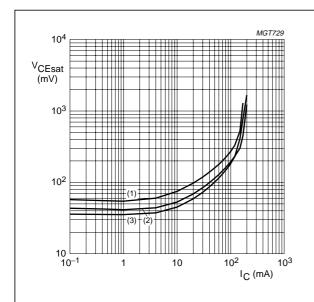
Fig.6 DC current gain as a function of collector current; typical values.



**BC847B**; V<sub>CE</sub> = 5 V.

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

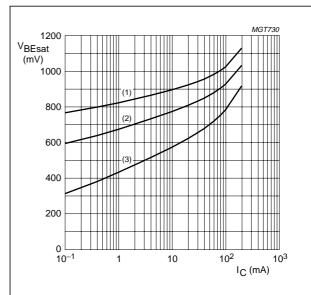
Fig.7 Base-emitter voltage as a function of collector current; typical values.



**BC847B**;  $I_C/I_B = 20$ .

- (1) T<sub>amb</sub> = 150 °C.
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



**BC847B**;  $I_C/I_B = 10$ .

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.9 Base-emitter saturation voltage as a function of collector current; typical values.

### NPN general purpose transistors

### BC846; BC847; BC848

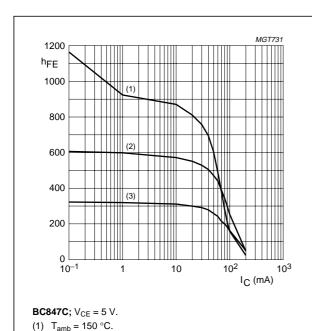
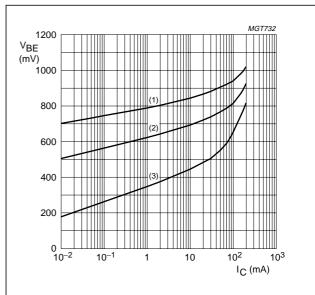


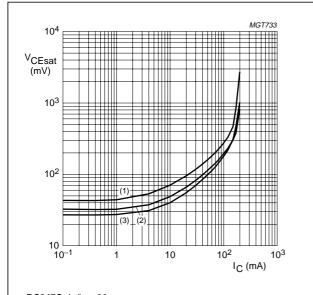
Fig.10 DC current gain as a function of collector current; typical values.



**BC847C**; V<sub>CE</sub> = 5 V.

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.11 Base-emitter voltage as a function of collector current; typical values.

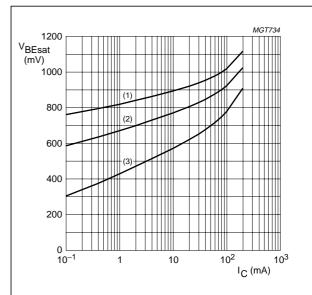


**BC847C**;  $I_C/I_B = 20$ .

(2)  $T_{amb} = 25 \,^{\circ}\text{C}$ . (3)  $T_{amb} = -55 \,^{\circ}\text{C}$ .

- (1) T<sub>amb</sub> = 150 °C.
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.12 Collector-emitter saturation voltage as a function of collector current; typical values.



**BC847C**;  $I_C/I_B = 10$ .

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

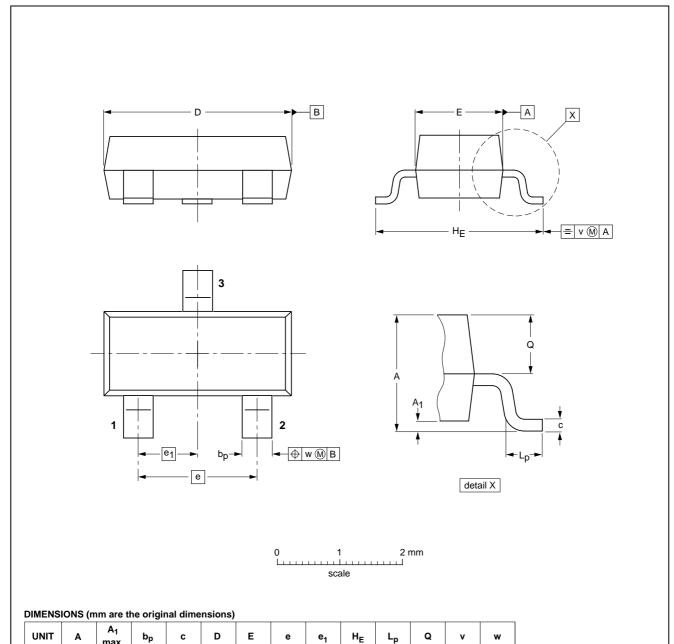
# NPN general purpose transistors

BC846; BC847; BC848

### **PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

SOT23



OUTLINE	REFERENCES		EUROPEAN	ICCUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT23		TO-236AB				<del>-97-02-28</del> 99-09-13

0.95

0.45 0.15 0.55 0.45

0.1

2002 Feb 04 8

0.48

0.38

0.1

mm

0.15

0.09

3.0 2.8 1.4 1.2

1.9

### NPN general purpose transistors

BC846; BC847; BC848

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# NPN general purpose transistors

BC846; BC847; BC848

### **NOTES**

# NPN general purpose transistors

BC846; BC847; BC848

### **NOTES**

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